

IN THE CLAIMS:

Please cancel Claims 1 to 3, 5 to 8, 10 to 29, 31 to 34, and 36 to 52 without prejudice to or disclaimer of the subject matter presented therein. Please amend Claims 4, 9, 30, and 35 as shown below.

Do Not  
Enter  
8/7/04  
m)

1 to 3. (Cancelled)

4. (Currently Amended) The A liquid phase growth process according to claim 1, comprising the steps of:

immersing a substrate in a melt held in a crucible, a crystal material having been dissolved in the melt; and

growing a crystal on the substrate,

wherein the crucible is rotated independently from the substrate during crystal growth,

wherein the substrate is disposed at a position set aside from the center of rotation of the crucible, and the crystal is grown on the surface of the substrate thus disposed,

wherein no part of the substrate is disposed at the center of rotation of the crucible, and

wherein a flow adjusting means is provided stationarily in the melt to make the flow of the melt inclined toward the center of rotation and/or the liquid surface of the melt.